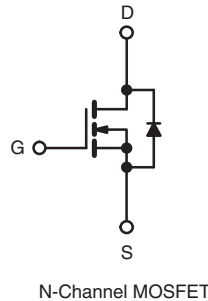
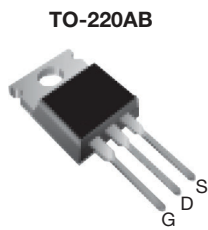


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	200 V
$R_{DS(on)}$ (Ω)	$V_{GS} = 5$ V 0.40
Q_g (Max.) (nC)	40
Q_{gs} (nC)	5.5
Q_{gd} (nC)	24
Configuration	Single



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Logic Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS} = 4$ V and 5 V
- 150 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRL630PbF SiHL630-E3
SnPb	IRL630 SiHL630

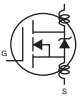
ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	200	V	
Gate-Source Voltage		V_{GS}	± 10		
Continuous Drain Current	V_{GS} at 5.0 V	I_D	$T_C = 25$ °C	9.0	A
			$T_C = 100$ °C	5.7	
Pulsed Drain Current ^a		I_{DM}	36		
Linear Derating Factor			0.59	W/°C	
Single Pulse Avalanche Energy ^b		E_{AS}	250	mJ	
Repetitive Avalanche Current ^a		I_{AR}	9.0	A	
Repetitive Avalanche Energy ^a		E_{AR}	7.4	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	74	W	
Peak Diode Recovery dV/dt^c		dV/dt	5.0	V/ns	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d		
Mounting Torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 4.6$ mH, $R_g = 25$ Ω , $I_{AS} = 9.0$ A (see fig. 12).
- $I_{SD} \leq 9.0$ A, $dV/dt \leq 120$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

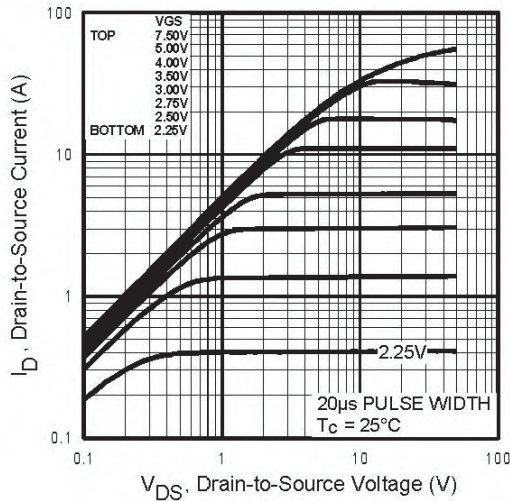
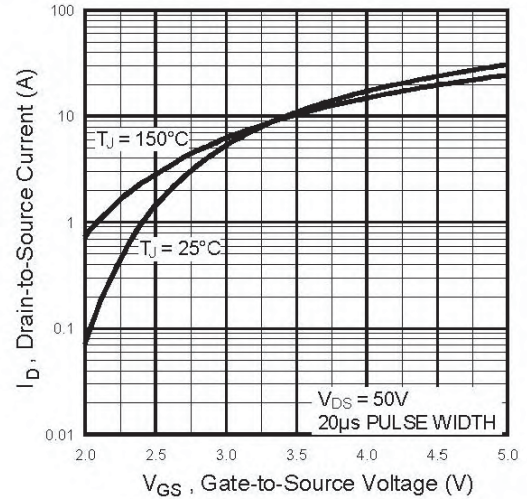
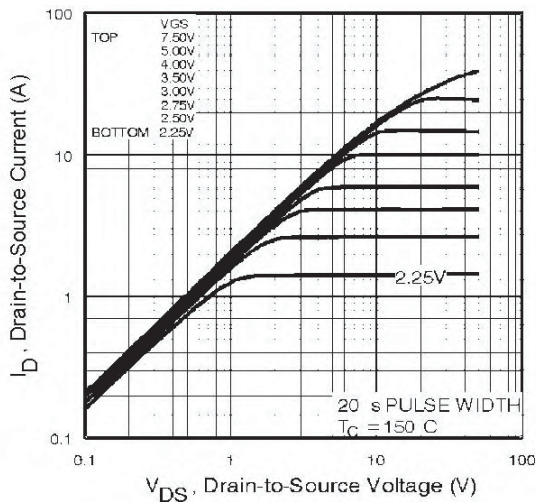
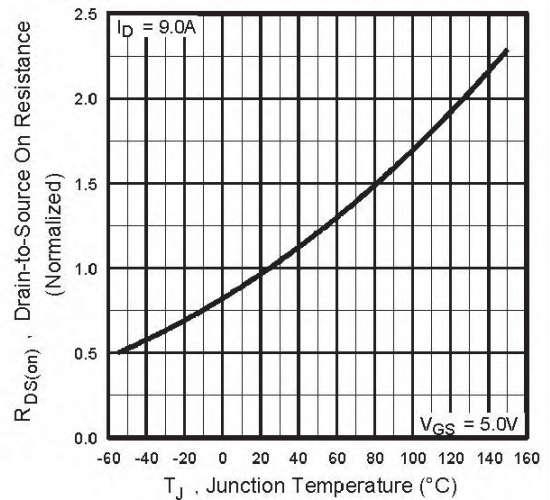
* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.27	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.0	-	2.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 160\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 5.0\text{ V}$, $I_D = 5.4\text{ A}^b$	-	-	0.40	Ω
		$V_{GS} = 4.0\text{ V}$, $I_D = 4.5\text{ A}^b$	-	-	0.50	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 5.4\text{ A}^b$	4.8	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$, see fig. 5	-	1100	-	μF
Output Capacitance	C_{oss}		-	220	-	
Reverse Transfer Capacitance	C_{rss}		-	70	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 9.0\text{ A}$, $V_{DS} = 160\text{ V}$, see fig. 6 and 13 ^b	-	-	40	nC
Gate-Source Charge	Q_{gs}		-	-	5.5	
Gate-Drain Charge	Q_{gd}		-	-	24	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$, $I_D = 9.0\text{ A}$ $R_g = 6.0\text{ }\Omega$, $R_D = 11\text{ }\Omega$, see fig. 10 ^b	-	8.0	-	ns
Rise Time	t_r		-	57	-	
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	
Fall Time	t_f		-	33	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode	-	-	9.0	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	36	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 9.0\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 9.0\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}^b$	-	230	350	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.7	2.6	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature

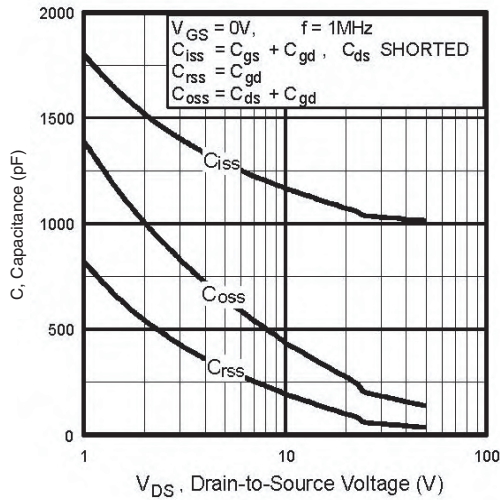


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

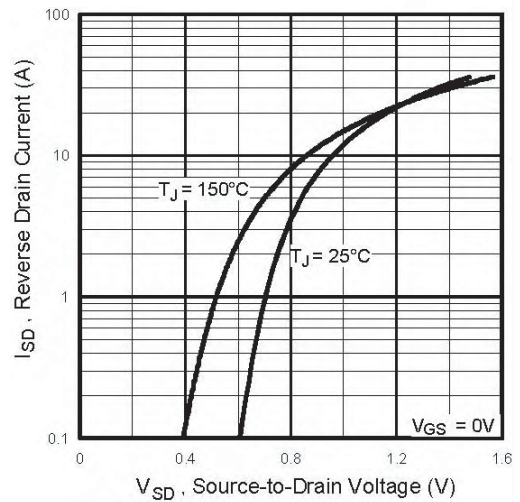


Fig. 7 - Typical Source-Drain Diode Forward Voltage

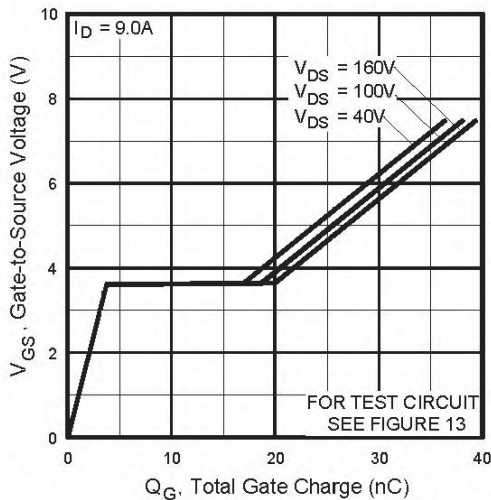


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

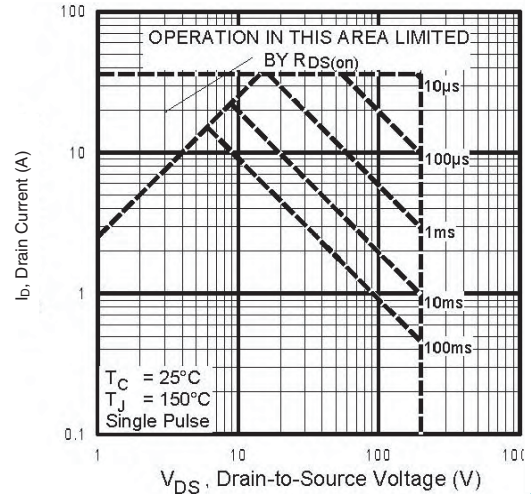


Fig. 8 - Maximum Safe Operating Area

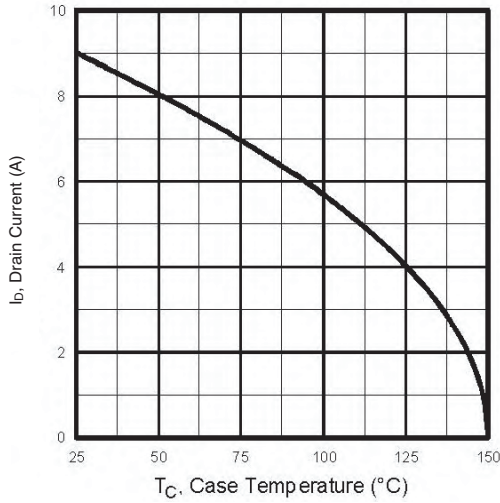


Fig. 9 - Maximum Drain Current vs. Case Temperature

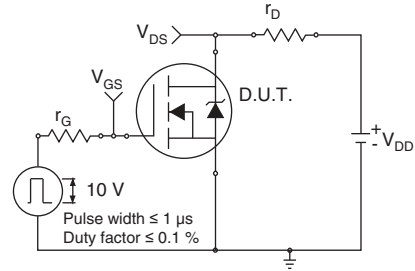


Fig. 10a - Switching Time Test Circuit

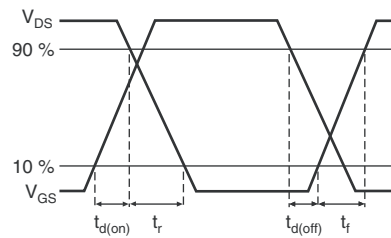


Fig. 10b - Switching Time Waveforms

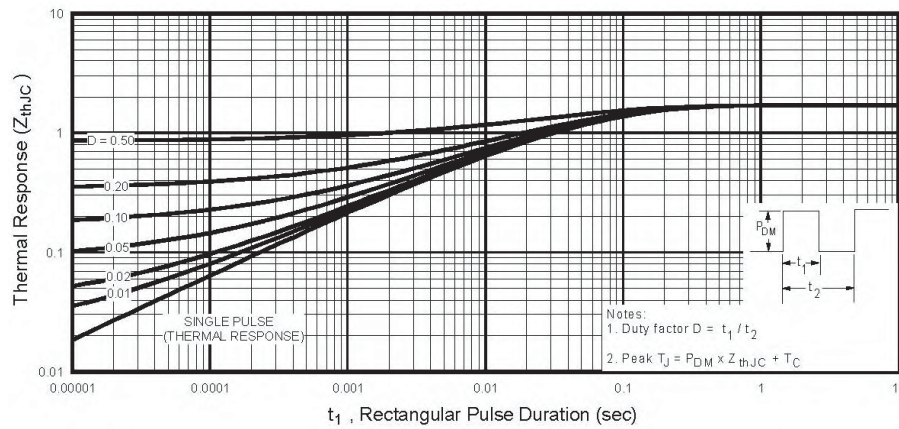


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

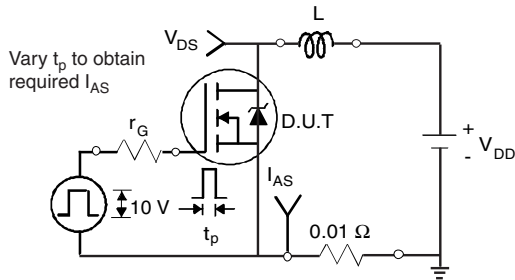


Fig. 12a - Unclamped Inductive Test Circuit

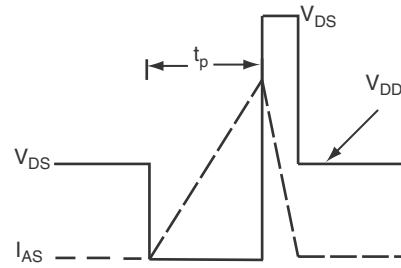


Fig. 12b - Unclamped Inductive Waveforms

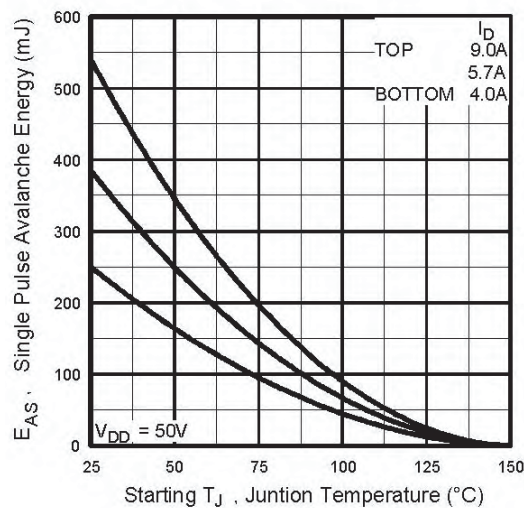


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

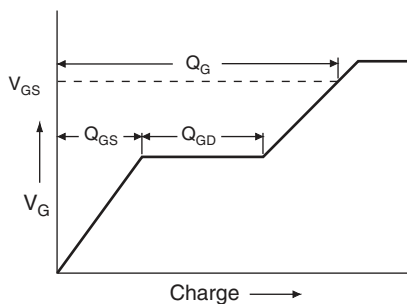


Fig. 13a - Basic Gate Charge Waveform

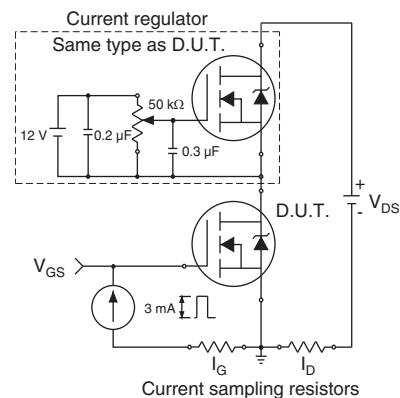
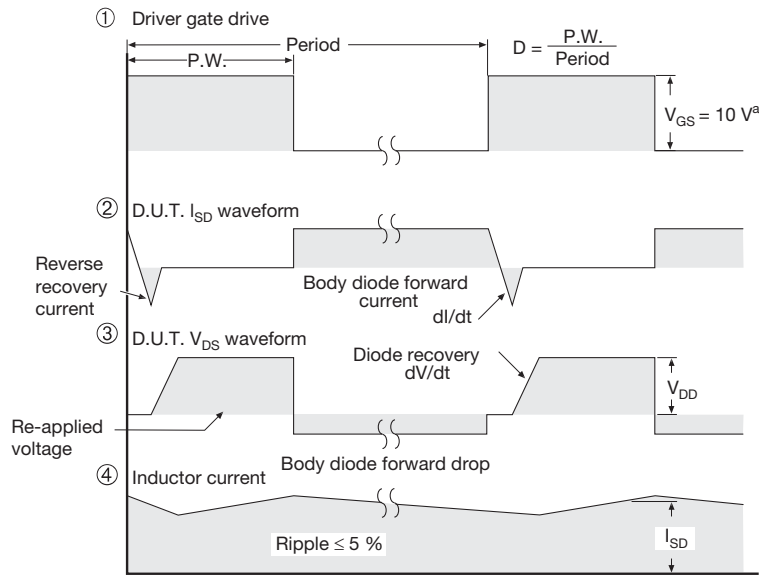
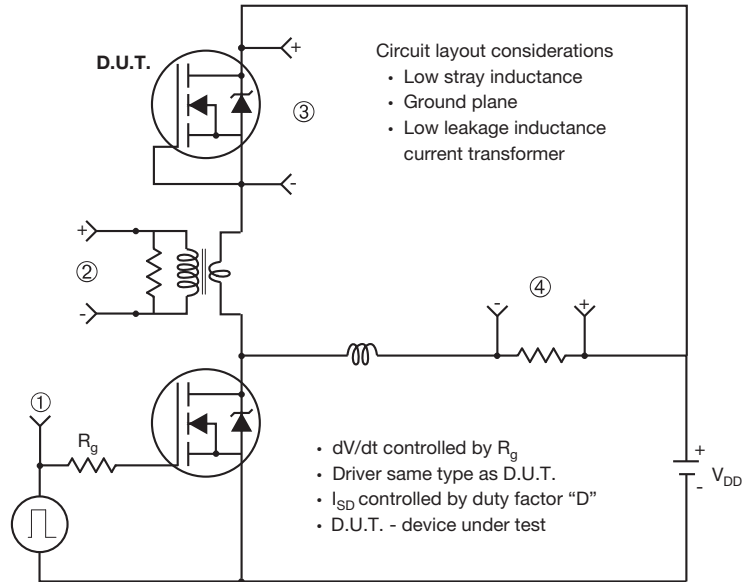


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

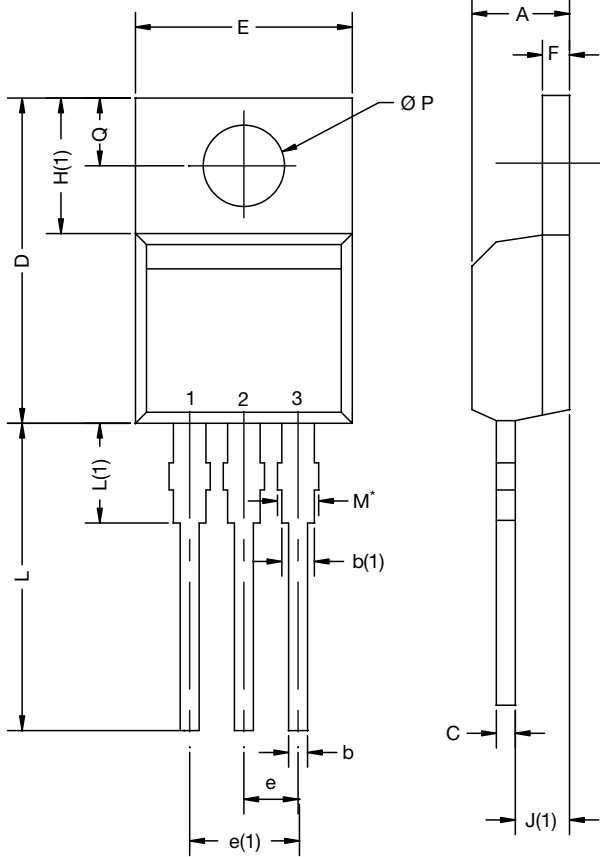


Note
a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91303.

TO-220-1

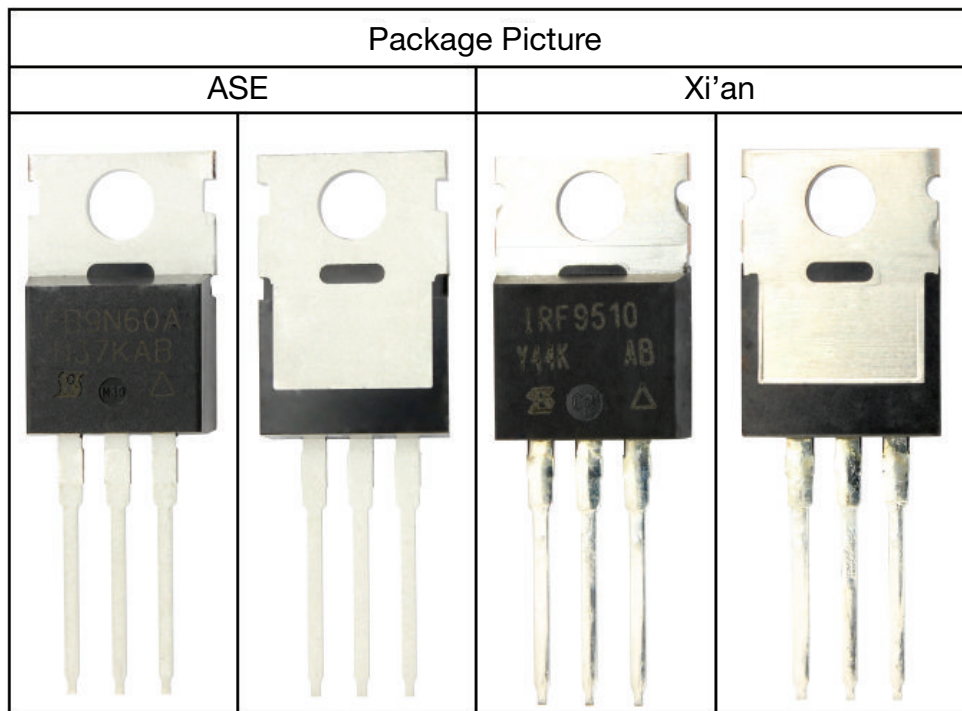


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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